

#2 / Pre-AmdtA  
11-14-01  
Dade

Box AF  
Commissioner for Patents  
Washington, D.C. 20231

Sir:

Prior to examining the instant application on the merits, please amend the specification as follows:

IN THE SPECIFICATION

A1

Please amend the specification by inserting before the first line the sentence --This is a continuation of U.S. Application No. 09/251,890, now pending.--

IN THE CLAIMS

✓  
1.-37. Canceled.

38. A method of fabricating a ferroelectric PZT film on a substrate, comprising forming the film by liquid delivery MOCVD on the substrate under MOCVD conditions producing a ferroelectric PZT material having at least one scalable character selected from the group consisting of dimensionally scalable character, pulse length scalable character and E-field scalable character, and wherein said PZT material has at least one of property selected from the group consisting of having a thickness from about 20 to about 150 nanometers, having a ferroelectric operating voltage below 2 Volts, having at least one Type 1 properties and having at least one Type 2 properties. [according to any one of claims 1 to 29].

56. A method of fabricating a ferroelectric PZT film on a substrate, comprising forming the film by liquid delivery MOCVD on the substrate under MOCVD conditions including nucleation conditions producing a ferroelectric PZT material having at least one scalable character selected from the group consisting of dimensionally scalable character, pulse length scalable character and E-field scalable character, and wherein said PZT material has at least one of

A3  
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